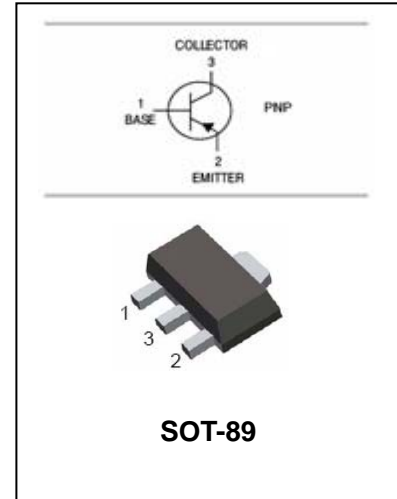


PNP Silicon Planar Medium Power High Performance Transistor FCX591

FEATURES

- Complementary type: FCX491.



ORDERING INFORMATION

Type No.	Marking	Package Code
FCX591	P1	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_{CM}	Peak Pulse Current	-2	A
I_C	Collector Current -Continuous	-1	A
I_B	Base Current	-0.2	A
P_D	Power Dissipation	1	W
T_j, T_{stg}	Junction and Storage Temperature	-65 to +150	°C

PNP Silicon Planar Medium Power High Performance Transistor FCX591

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60V$			-100	nA
Collector-Emitter Cut-Off Current	I_{CES}	$V_{CES}=-60V$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-3V, I_C=0$			-100	nA
DC current gain	h_{FE}	$V_{CE}=-5V, I_C=-1mA$ $V_{CE}=-5V, I_C=-500mA$ $V_{CE}=-5V, I_C=-1A$ $V_{CE}=-5V, I_C=-2A$	100 100 80 15	300		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$ $I_C=-1A, I_B=-100mA$			-0.3 -0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-1A, I_B=-100mA$			-1.2	V
Base-emitter Turn-on Voltage	$V_{BE(on)}$	$I_C=-1A, V_{CE}=-5V$			-1.0	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA,$ $f=100MHz$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$			10	pF

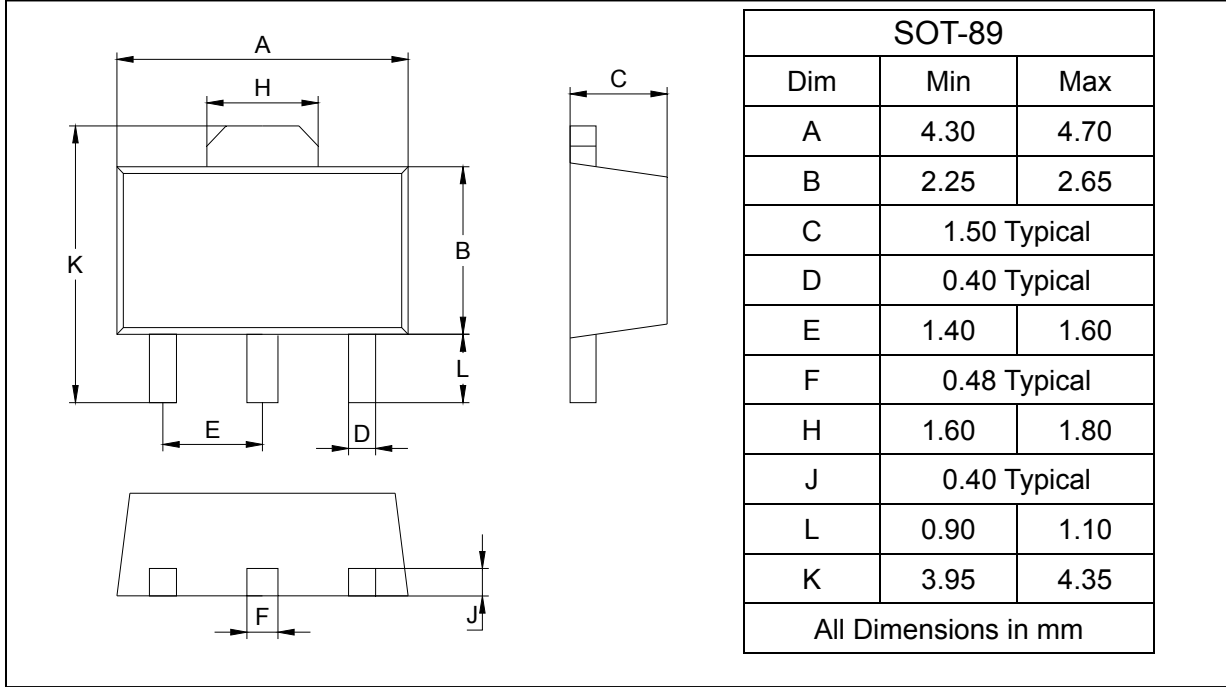
PNP Silicon Planar Medium Power High Performance Transistor

FCX591

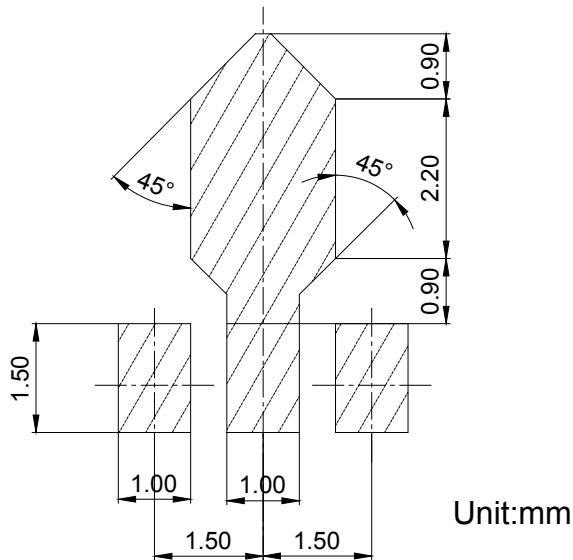
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
FCX591	SOT-89	1000/Tape&Reel